

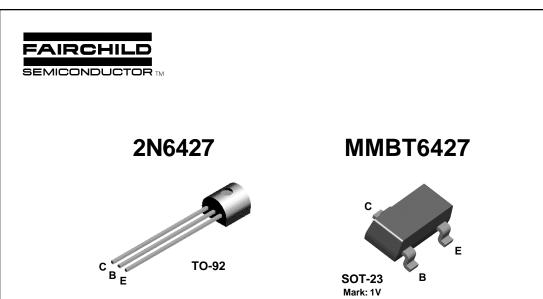
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NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current - Continuous	1.2	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic Max		Units	
		2N6427	*MMBT6427	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/∘C
$R_{ ext{ ext{ ext{ ext{ ext{ ext{ ext{ ext$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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NPN Darlington Transistor

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(continued)

TERISTICS			·	
ector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
ector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	40		V
tter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	12		V
ector Cutoff Current	$V_{CE} = 25 \text{ V}, \text{ I}_{B} = 0$		1.0	μA
ector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		50	nA
tter Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$		50	nA
	ector-Base Breakdown Voltage tter-Base Breakdown Voltage ector Cutoff Current ector Cutoff Current tter Cutoff Current	tter-Base Breakdown Voltage $I_E = 10 \ \mu A, I_C = 0$ ector Cutoff Current $V_{CE} = 25 \ V, I_B = 0$ ector Cutoff Current $V_{CB} = 30 \ V, I_E = 0$	tter-Base Breakdown Voltage $I_E = 10 \ \mu$ A, $I_C = 0$ 12ector Cutoff Current $V_{CE} = 25 \ V$, $I_B = 0$ ector Cutoff Current $V_{CB} = 30 \ V$, $I_E = 0$	tter-Base Breakdown Voltage $I_E = 10 \ \mu$ A, $I_C = 0$ 12ector Cutoff Current $V_{CE} = 25 \ V$, $I_B = 0$ 1.0ector Cutoff Current $V_{CB} = 30 \ V$, $I_E = 0$ 50

	$v_{EB} = 10 v, I_C = 0$		50	nA
ACTERISTICS				
DC Current Gain*	I _C = 10 mA, V _{CE} = 5.0 V	10,000	100,000	
	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$	20,000	200,000	
	$I_{C} = 500 \text{ mA}, V_{CE} = 5.0 \text{ V}$	14,000	140,000	
Collector-Emitter Saturation Voltage	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.2	V
-	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.5	V
Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
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SMALL SIGNAL CHARACTERISTICS

Base-Emitter On Voltage

V_{CE(sat)}

V_{BE(sat)}

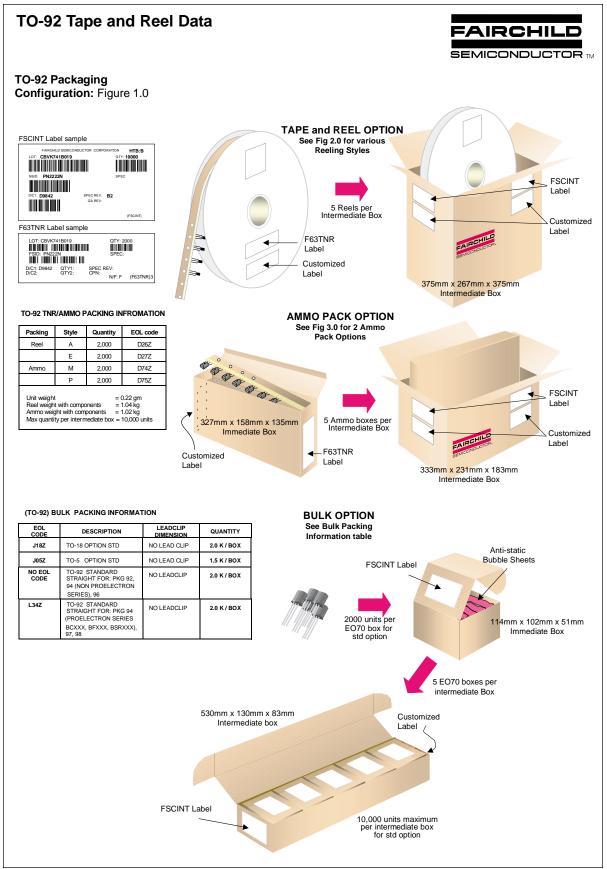
V_{BE(on)}

C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ f = 1.0 MHz	7.0	pF
C _{ibo}	Input Capcitance	$V_{BE} = 1.0 \text{ V}, I_{C} = 0,$ f = 1.0 MHz	15	pF

 I_{C} = 50 mA, V_{CE} = 5.0 mA

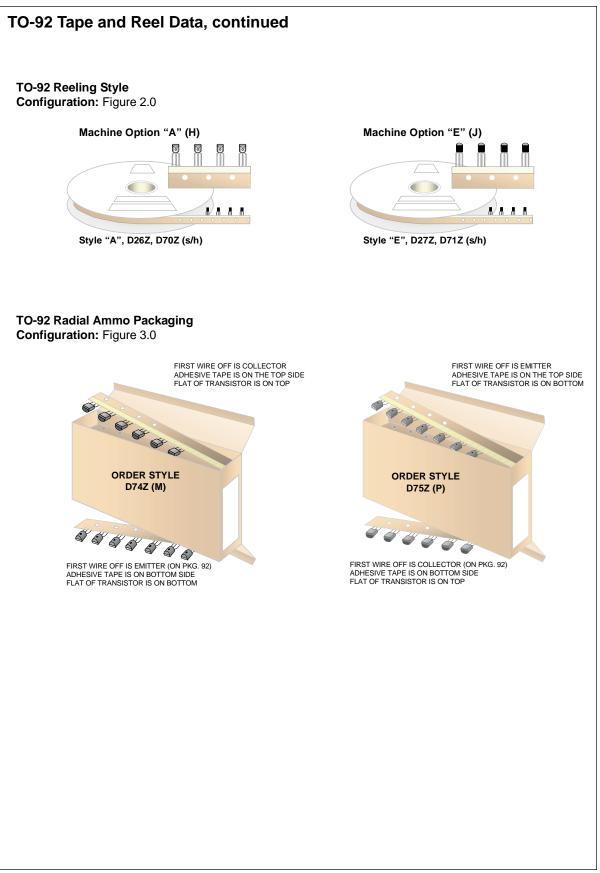
*Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

2N6427 / MMBT6427



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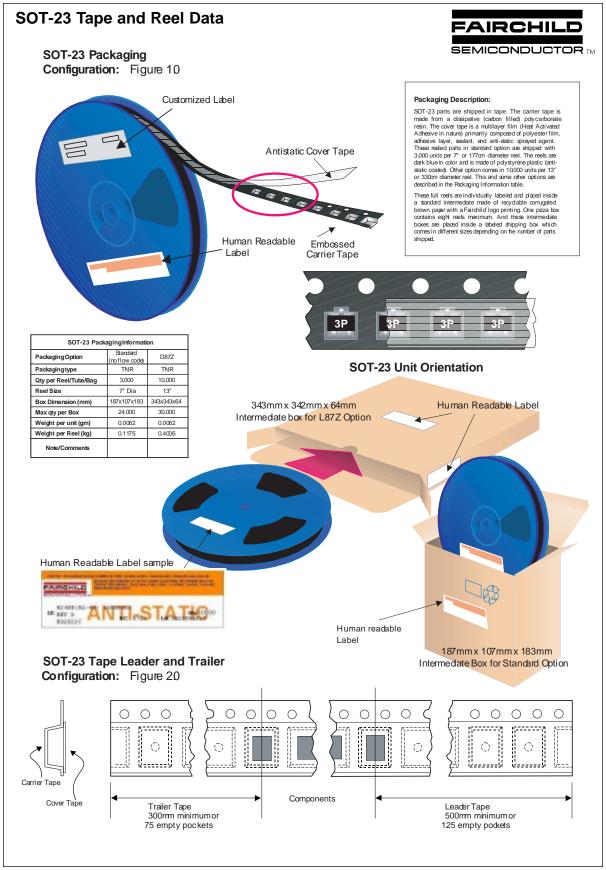
March 2001, Rev. B1





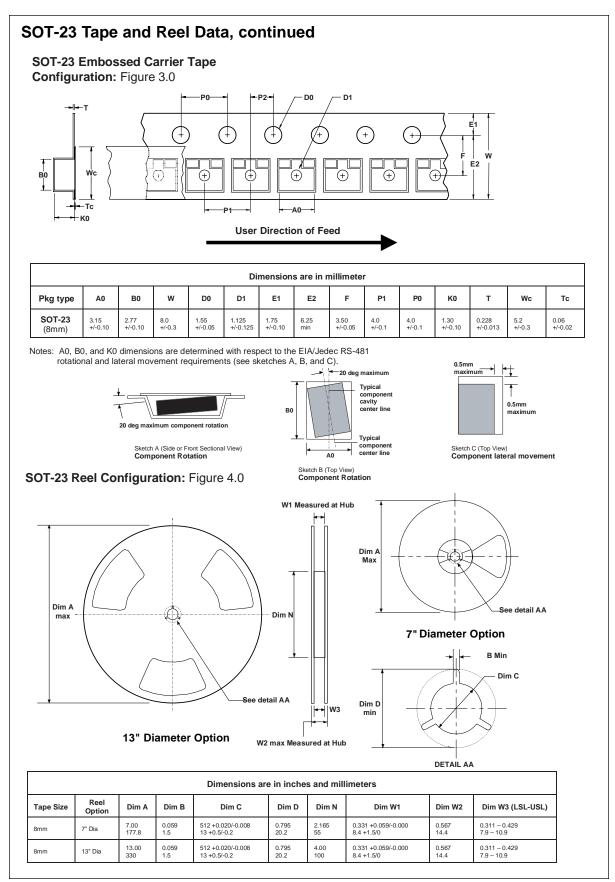
July 1999, Rev. A



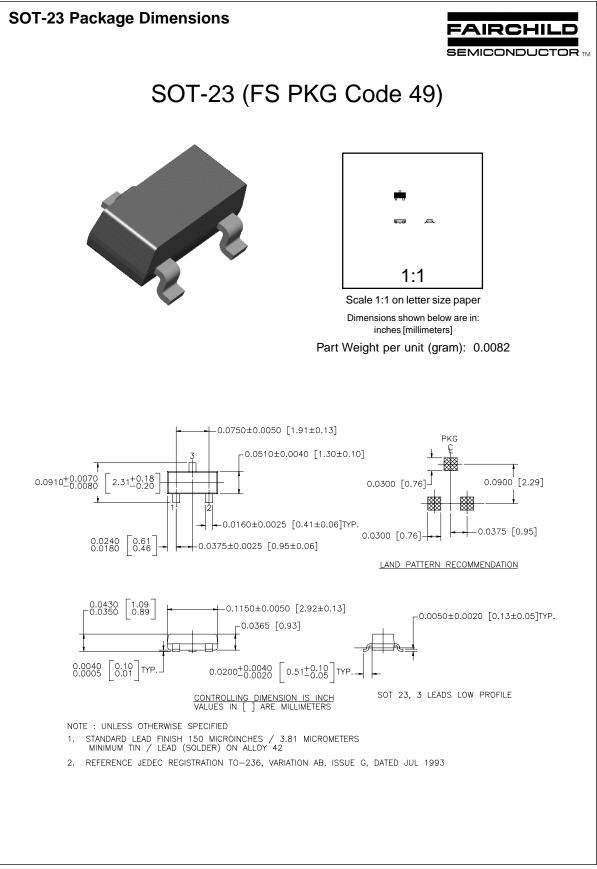


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Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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